

SILICON NPN TRIPLE DIFFUSED TYPE

2SC2793

HIGH SPEED AND HIGH VOLTAGE SWITCHING APPLICATIONS.
 SWITCHING REGULATOR APPLICATIONS.
 HIGH SPEED DC-DC CONVERTER APPLICATIONS.

FEATURES:

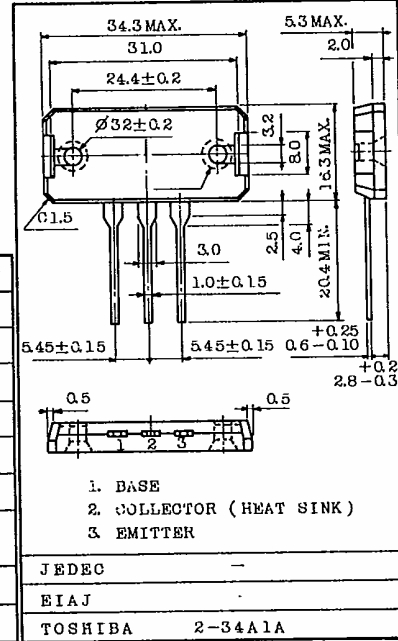
- Excellent Switching Times
 : $t_r=1.0\mu s$ (Max.), $t_f=1.0\mu s$ (Max.) ($I_C=3A$)
- High Collector Breakdown Voltage : $V_{CE0}=800V$

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	900	V
Collector-Emitter Voltage	V_{CE0}	800	V
Emitter-Base Voltage	V_{EB0}	7	V
Collector Current	DC	5	A
	Peak	7	A
Base Current	I_B	3	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	100	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

INDUSTRIAL APPLICATION

Unit in mm



Weight : 10.8g

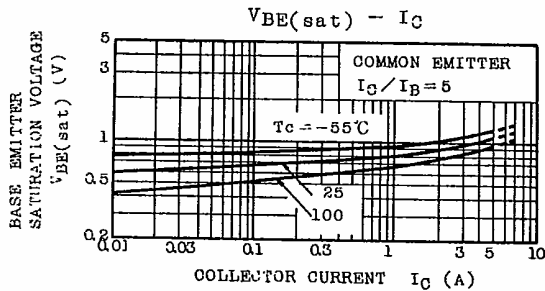
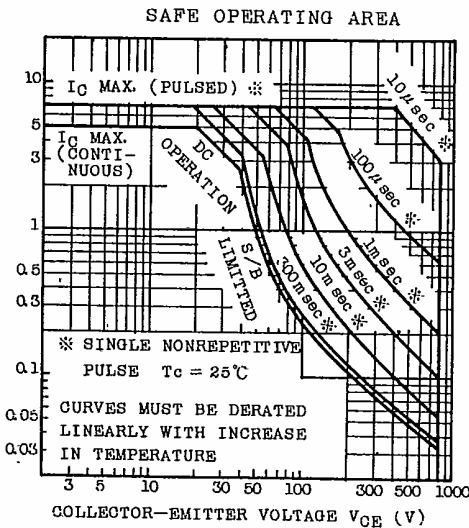
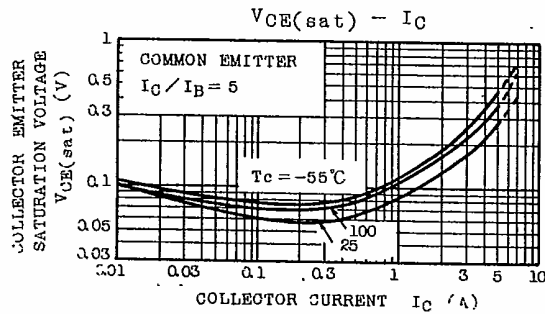
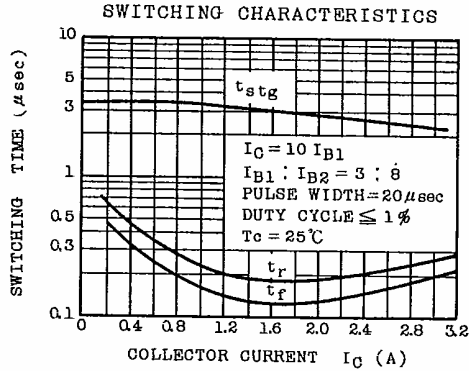
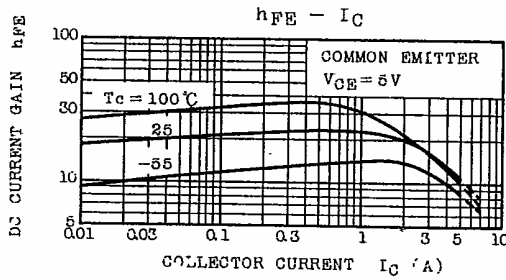
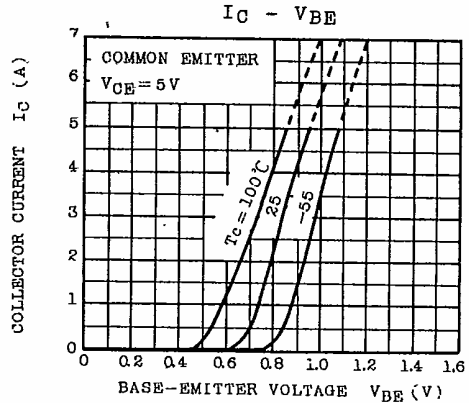
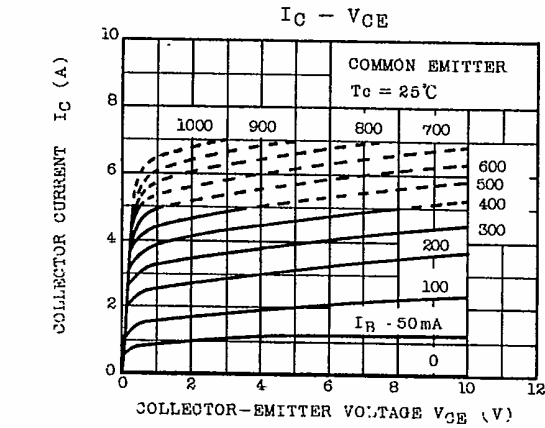
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=800V, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$	-	-	1	mA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	900	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	800	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=10mA$ (Note)	10	-	-	-
	$h_{FE(2)}$	$V_{CE}=5V, I_C=3A$ (Note)	10	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=0.6A$ (Note)	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=3A, I_B=0.6A$ (Note)	-	-	1.5	V
Switching Time	Rise Time	t_r	-	-	1.0	μs
	Storage Time	t_{stg}	-	-	3.5	
	Fall Time	t_f	-	-	1.0	

Note: Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

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